IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No
Priority Filing DateJune 11, 1999
nventor
Assignee Micron Technology, Inc.
<u>Priority</u> Group Art Unit
<u>Priority</u> Examiner
Attorney's Docket No Ml22-1741
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects,
and Wordline. Transistor Gate, and Conductive Interconnect Structures

PRELIMINARY AMENDMENT

To:

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

D. Brent Kenady (Tel. 509-624-4276; Fax 509-838-3424)

Wells, St. John, Roberts, Gregory & Matkin P.S.

601 W. First Avenue, Suite 1300 Spokane, WA 99201-3828

<u>AMENDMENTS</u>

In the Specification

At page 1, before the "Technical Field" section, insert the following paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

~RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/332,271, filed June 11, 1999.—.

H. W. T. C. B. W. W. C. B. W.